

**Amendments to the Specification:**

Please replace the paragraph beginning at page 8, line 1, with the following rewritten paragraph:

Plate 18 and a circumferential wall 19 made of an insulator. A plasma generation chamber 21 is formed inside. The plasma generation chamber 21 is connected to the film deposition chamber 13 outside the plasma generator 14 through a plurality of through holes 18a formed on the lower plate 18. A high frequency power supply 22 is connected to the upper plate 17. High frequency power is supplied to the upper plate 17. An insulator 24 is provided between the power feed line 23 and the chamber vessel 40. Further, the plasma generator 14 is provided with a first gas feeder 26 for feeding a film deposition gas to the plasma generation chamber 21 through the valve 25 and a second gas feeder 28 for feeding a cleaning gas to the plasma generation chamber 21 through the valve 27. As the film deposition gas, for example,  $\text{NH}_3$ ,  $\text{NH}_2$ ,  $\text{O}_2$ ,  $\text{H}_2$ , Ar, etc. is used. Further, as the cleaning gas, for example,  $\text{NH}_3$ ,  $\text{ClF}_3$ ,  $\text{CF}_4$ ,  $\text{C}_2\text{F}_6$ ,  $\text{H}_2$ ,  $\text{O}_2$ ,  $\text{H}_2$ ,  $\text{F}_2$ , Ar,  $\text{SF}_3$ , etc. (~~dilute gas~~noble gas or rare gas, halide gas, etc.) is used. On the other hand, the lower plate 18 is connected to the ground